

# InGaP/InGaAs-on-Ge Concentrator Solar Cell for Space Power Generation

Contract—

NAS3-99174

Author—

Samar Sinharoy

Date—

October 12, 2000

Contractor—

Essential Research, Inc.  
6410 Eastland Rd.  
Suite D  
Cleveland, OH 44142

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**WORK PERFORMED DURING THIS PERIOD**

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***Task 1: Growth and characterization of a lattice-matched passivating window for InGaP***

$\text{Al}_{0.33}\text{In}_{0.67}\text{P}$  has been chosen as the lattice-matched passivating front and back window layer of the 1.62-eV InGaP top cell. As described in the previous report, secondary electron mass spectrometry (SIMS) analysis of the films revealed that the oxygen concentration in these films was in the low to mid- $10^{17}/\text{cm}^3$  level. In order to reduce the oxygen content in the AlInP window layer, we are planning to replace our precursor for aluminum (TMAI) with an ultra-pure, very low oxygen containing TMAI source. This should be accomplished within the next month.

***Task 4. Fabrication and testing of two-terminal InGaP/InGaAs monolithic tandem cells on GaAs substrates.***

Figure 1 shows a schematic diagram of the current design of our dual-junction cell. The 1.1-eV bottom cell is comprised of a 0.5- $\mu\text{m}$  n+  $\text{In}_{0.2}\text{Ga}_{0.8}\text{As}$  emitter, a 3.0- $\mu\text{m}$  p  $\text{In}_{0.2}\text{Ga}_{0.8}\text{As}$  base and a 0.05- $\mu\text{m}$   $\text{In}_{0.68}\text{Ga}_{0.32}\text{P}$  window layer. The 1.62-eV top cell in the initial design<sup>5</sup> consisted of a 0.05- $\mu\text{m}$  n+  $\text{In}_{0.68}\text{Ga}_{0.32}\text{P}$  emitter, a 1.5- $\mu\text{m}$  p  $\text{In}_{0.68}\text{Ga}_{0.32}\text{P}$  base, a 0.05- $\mu\text{m}$  p+  $\text{In}_{0.68}\text{Ga}_{0.32}\text{P}$  back surface field, and a 0.05- $\mu\text{m}$  n  $\text{Al}_{0.33}\text{In}_{0.67}\text{P}$  window layer. We have thinned the top cell in the current design as described below. A p++/n++  $\text{In}_{0.2}\text{Ga}_{0.8}\text{As}$  tunnel junction test structure, with the same thickness (0.05  $\mu\text{m}$ ) and doping levels ( $1 \times 10^{19}/\text{cm}^3$ ) used in the dual-junction cell was evaluated prior to its incorporation in the dual-junction cell. We have chosen to use InGaAs as the tunnel junction interconnect compound since it is easily degenerately doped. All of the dual-junction cell structures were grown on GaAs substrates. Time constraints prevented us from completing the development of the GaAs-on-Ge growth process. As a result, no cell structures were grown on GaAs-coated Ge.

Contact		
n++	In <sub>0.2</sub> Ga <sub>0.8</sub> As	0.1 μm
n	Al <sub>0.33</sub> In <sub>0.67</sub> P	0.04 μm
n+	In <sub>0.68</sub> Ga <sub>0.32</sub> P	0.05 μm
p	In <sub>0.68</sub> Ga <sub>0.32</sub> P	0.3 μm
p+	In <sub>0.68</sub> Ga <sub>0.32</sub> P	0.05 μm
p	Al <sub>0.33</sub> In <sub>0.67</sub> P	0.05 μm
p++	In <sub>0.2</sub> Ga <sub>0.8</sub> As	0.02 μm
n++	In <sub>0.2</sub> Ga <sub>0.8</sub> As	0.02 μm
n+	In <sub>0.68</sub> Ga <sub>0.32</sub> P	0.05 μm
n	In <sub>0.2</sub> Ga <sub>0.8</sub> As	0.5 μm
p	In <sub>0.2</sub> Ga <sub>0.8</sub> As	3.0 μm
p	In <sub>0.68</sub> Ga <sub>0.32</sub> P	0.05 μm
Buffer Scheme		
p	GaAs	
	6° off towards (111)B	
Contact		

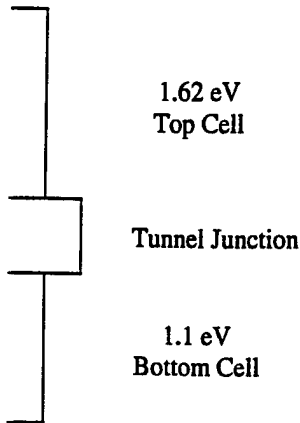


Figure 1. Epi-layer structure of the 1.62 eV InGaP/1.1 eV InGaAs dual-junction cell.

The first batch of 1.6-eV/1.1-eV dual-junction cells processed in our laboratory was bottom cell current limited.<sup>5</sup> This was believed to be one of the reasons for the low AM0, one-sun efficiency (12.9% without AR-coating, estimated to be 17% with an optimized anti-reflection coating) of those cells. Calculations have since shown that in order to obtain 100% quantum efficiency (QE) from the bottom cell, while maintaining a QE of at least 90% from the top cell, the top cell had to be thinned to 0.33 μm (compared to 1.65 μm in the first batch). Shown in Figure 2 is the light current-voltage (I-V) characteristic of a 1.62-eV/1.1-eV n/p dual-junction cell with a thinned top cell.<sup>5</sup> The cell is characterized by an open-circuit voltage (Voc) of 1.73 mV, a short-circuit current density (Jsc) of 19.14 mA, a fill factor (FF) of 78.5%, and an AM0, one-sun efficiency of 19.07%. The top cell in this case consisted of a 0.05-μm n+ In<sub>0.68</sub>Ga<sub>0.32</sub>P emitter, a 0.3-μm p In<sub>0.68</sub>Ga<sub>0.32</sub>P base, a 0.05-μm p+ In<sub>0.68</sub>Ga<sub>0.32</sub>P back surface field, and a 0.04-μm n Al<sub>0.33</sub>In<sub>0.67</sub>P window layer. The efficiency of this dual-junction cell, although higher than the first batch, is still significantly lower than the predicted value of 27%. The external quantum efficiency (EQE) of the subcells of the dual-junction cells was measured using appropriate filters, and the results are shown in Figure 3.

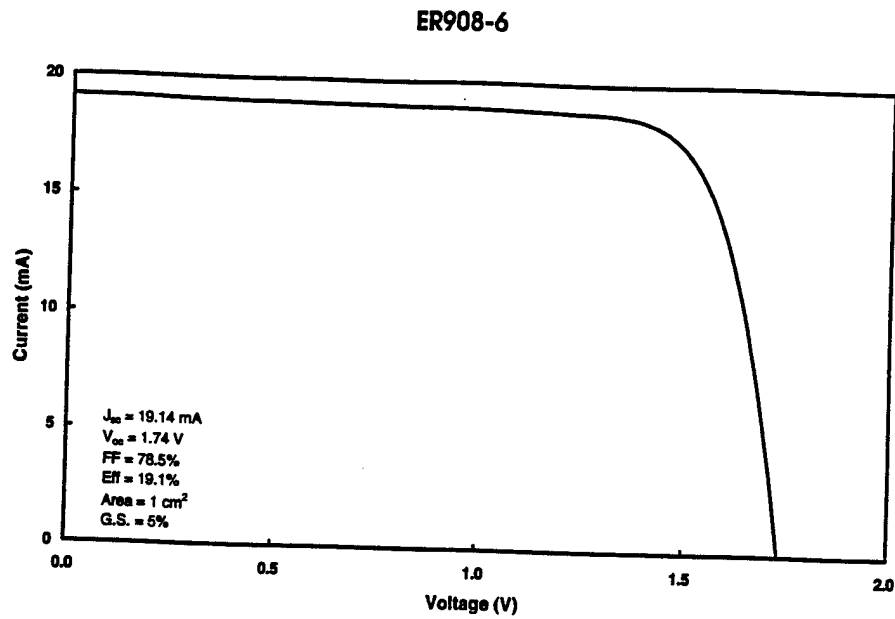


Figure 2.—I-V characteristics of an AR-coated  $1\text{-cm}^2$  1.62-eV n/p InGaP/1.1-eV InGaAs dual-junction cell.

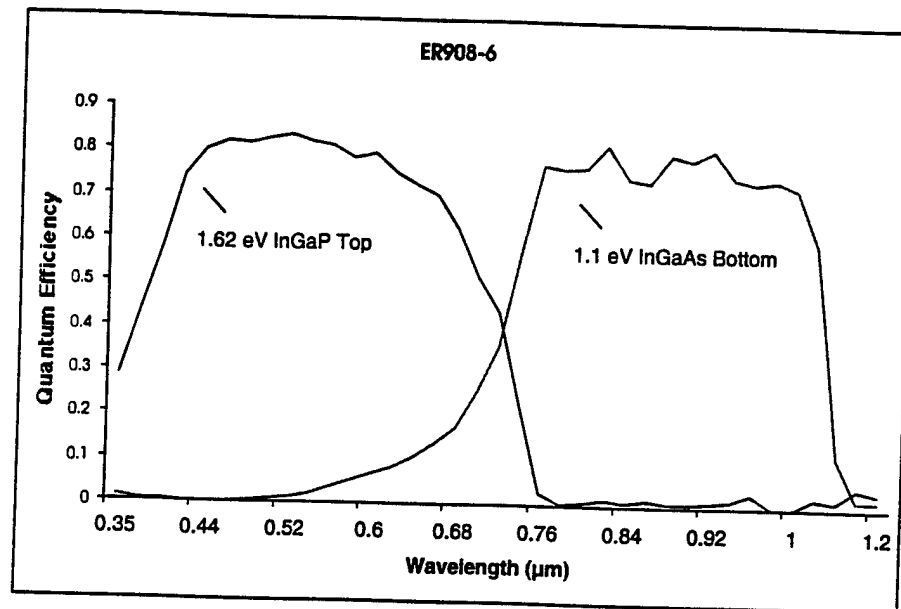


Figure 3.—External quantum efficiency of the subcells of a  $1\text{-cm}^2$  1.62-eV n/p InGaP/ 1.1-eV InGaAs dual-junction cell.

## **CURRENT PROBLEMS AND PROPOSED CORRECTIVE ACTIONS**

Analysis of the I-V and EQE data and comparison with computer modeled data shows that the performance of the dual-junction cell is still being controlled by the bottom cell, in spite of the top cell thinning. This is evidenced by the fact that the measured AM0, Jsc of the dual-junction cell prior to AR-coating was  $14.4 \text{ mA/cm}^2$ , whereas the Jsc of the stand-alone InGaP cell under similar conditions was  $15.9 \text{ mA/cm}^2$ . If we further thin the top cell to achieve current matching conditions, then the Jsc of the dual-junction cell is expected to be the average of these two values, which is  $15.2 \text{ mA/cm}^2$ . The addition of an AR-coating will increase the value of the Jsc by a factor of 1.4, bringing it up to  $21.2 \text{ mA/cm}^2$ . Combining this Jsc with our experimental values of reverse saturation current density ( $J_0$ ) of  $1.7 \times 10^{-33} \text{ A}$  and a FF of 78.5%, we could obtain a Voc of 1.74 V, and an efficiency of 21.1%. Thus, optimization of top cell thinning alone will immediately improve the efficiency of the dual cell by 2 efficiency points.

Another factor limiting the performance of our dual-junction cell is the use of a 1.1-eV InGaAs tunnel junction, which absorbs some of the red light that the bottom cell is designed to convert. Calculations indicate that the use of a non-absorbing tunnel junction (such as 1.62-eV InGaP) would result in a 6% increase in the Jsc of the bottom cell. Since our dual-junction cell is bottom cell current-limited, this would increase the Jsc of the bottom cell to  $15.3 \text{ mA/cm}^2$  without AR-coating. If we thin the top cell to achieve current matching conditions, then following the same argument as in the previous paragraph, Jsc of the dual-junction cell would increase to  $15.6 \text{ mA/cm}^2$  without AR-coating, and to  $21.8 \text{ mA/cm}^2$  with AR-coating. This will bring the efficiency up to 21.8%, using the same calculations as in the previous paragraph. SIMS analysis of our dual-junction cell structure has shown no evidence of dopant diffusion from the tunnel junction into the active layers.

Further improvement in the dual-junction cell efficiency is possible by thinning the front window. Modeling has shown that while the actual front window thickness is  $400 \text{ \AA}$ , about half of the carriers generated therein are collected, so that the effective window thickness is only  $200 \text{ \AA}$ . If we reduce the actual window thickness to  $200 \text{ \AA}$ , we will have an effective window thickness of about  $100 \text{ \AA}$ . This would result in an efficiency of 22.1% for the dual-junction cell. Significant improvements in the AlInP window layer quality is anticipated when the unacceptably high oxygen concentration ( $1.0 \times 10^{17} \text{ /cm}^2$ ) in that layer is reduced. Calculations show that a perfect (no loss) window would result in a further improvement in efficiency from 22.1% to 24.3%.

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**WORK TO BE PERFORMED DURING THE NEXT PERIOD**

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During the next reporting period, the emphasis will be on large area pulse solar simulator (LAPPS) testing of the individual InGaP and InGaAs cells under 1 to 20 sun concentrations. These tests could not be done during the current reporting period, because the test facility at the Glenn research center is being rebuilt. The cell structures and processing parameters will continue to be optimized to realize the highest possible efficiency values under concentrator conditions. For the dual-junction cell, initial efforts during the next reporting period will be limited to optimizing the structure and processing to obtain the highest efficiency values under AM0, one-sun conditions, until the individual cell structures are optimized for higher concentrations.

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**COST AND COMPLETION ESTIMATES**

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The current costs have been calculated and the estimates are as follows:

- Total Costs (cumulative) through September 22, 2000..... \$ 82,406
- Estimated Costs for the following quarter..... \$ 50,000
- Estimated Costs to the contract completion ..... \$213,427
- Estimated physical completion through September 22, 2000 ..... 27%

REPORT DOCUMENTATION PAGE			Form Approved OMB No. 0704-0188	
Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503.				
1. AGENCY USE ONLY (Leave blank)	2. REPORT DATE October 12, 2000	3. REPORT TYPE AND DATES COVERED Interim - 6-month — 3/22/00 — 9/22/00		
4. TITLE AND SUBTITLE InGaP/InGaAs-on-Ge Concentrator Solar Cell for Space Power Generation		5. FUNDING NUMBERS  NAS3-99174		
6. AUTHOR(S)  Dr. Samar Sinharoy				
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES)  Essential Research, Inc. 23811 Chagrin Blvd., Suite 280 Cleveland, OH 44122		8. PERFORMING ORGANIZATION REPORT NUMBER  NAS3-99174		
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES)  National Aeronautics and Space Administration Glenn Research Center 21000 Brookpark Rd. Cleveland, OH 44135		10. SPONSORING/MONITORING AGENCY REPORT NUMBER		
11. SUPPLEMENTARY NOTES				
12a. DISTRIBUTION/AVAILABILITY STATEMENT  Unclassified – Unlimited		12b. DISTRIBUTION CODE		
13. ABSTRACT (Maximum 200 words)  The passivating front and back window layer of the top cell has been chosen.  We have chosen to use InGaAs as the tunnel junction interconnect compound since it is easily degenerately doped. All of the dual junction cell structures were grown on GaAs substrates. Time constraints prevented us from completing the development of the GaAs-on-Ge growth process.  Analysis of the I-V and EQE data, and comparison with computer-modeled data, shows that the performance of the dual-junction cell is still being controlled by the bottom cell, in spite of top cell thinning. Further improvement in the dual-junction cell efficiency is possible by thinning the front window.				
14. SUBJECT TERMS  Space Power; photovoltaics; Indium Gallium Phosphide; Concentrator Solar Cells			15. NUMBER OF PAGES 7	
			16. PRICE CODE	
17. SECURITY CLASSIFICATION OF REPORT Unclassified	18. SECURITY CLASSIFICATION OF THIS PAGE Unclassified	19. SECURITY CLASSIFICATION OF ABSTRACT Unclassified	20. LIMITATION OF ABSTRACT	